MOSFETs Silicon P-Channel MOS (U-MOSⅥ)

TJ80S04M3L

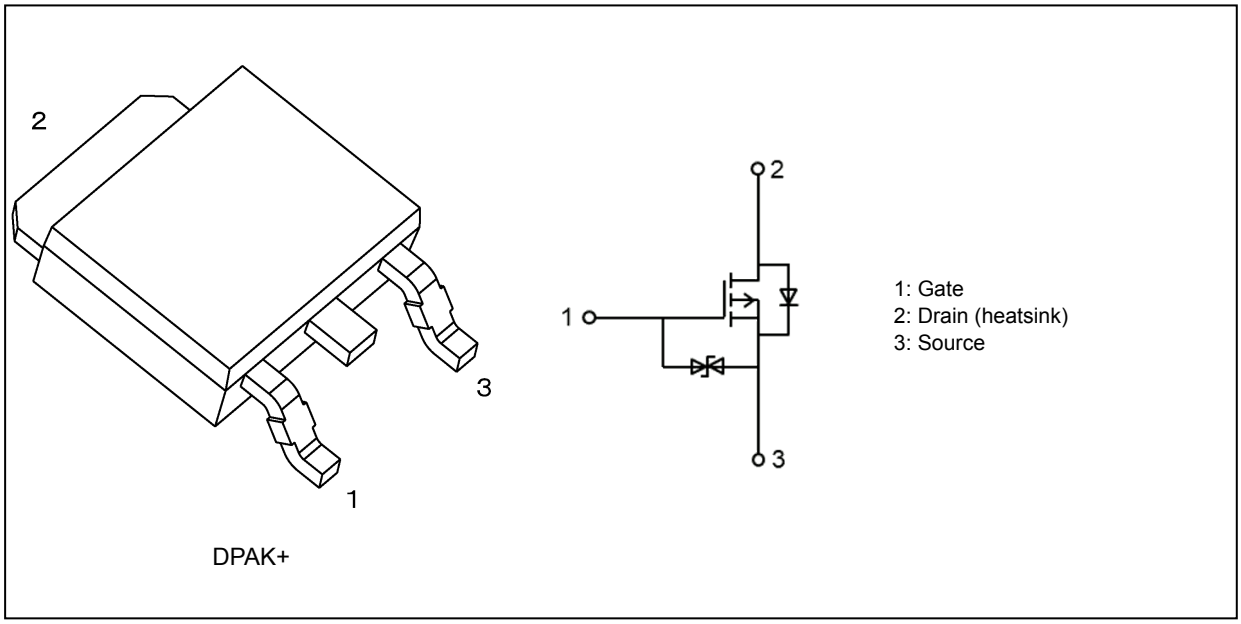
1. Applications

- Automotive
- Motor Drivers
- DC-DC Converters
- Switching Voltage Regulators

2. Features

(1) AEC-Q101 qualified
(2) Low drain-source on-resistance: $R_{DS(ON)}$ = 4.0 mΩ (typ.) (V_{GS} = -10 V)
(3) Low leakage current: I_{DSS} = -10 μA (max) (V_{DS} = -40 V)
(4) Enhancement mode: V_{th} = -2.0 to -3.0 V (V_{DS} = -10 V, I_D = -1 mA)

3. Packaging and Internal Circuit



Start of commercial production
2011-03

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4. Absolute Maximum Ratings (Note) (T_a = 25°C unless otherwise specified)

Characteristics		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	-40	V
Gate-source voltage		V_{GSS}	-20/+10	
Drain current (DC)	(Note 1)	I_D	-80	A
Drain current (pulsed)	(Note 1)	I_{DP}	-160	
Power dissipation	(T_c = 25°C)	P_D	100	W
Single-pulse avalanche energy	(Note 2)	E_{AS}	148	mJ
Avalanche current		I_{AR}	-80	A
Channel temperature	(Note 3)	T_{ch}	175	°C
Storage temperature	(Note 3)	T_{stg}	-55 to 175	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	$R_{th(ch-c)}$	1.5	°C/W

Note 1: Ensure that the channel temperature does not exceed 175°C.
Note 2: V_{DD} = -25 V, T_{ch} = 25°C (initial), L = 24 μH, R_G = 25 Ω, I_{AR} = -80 A
Note 3: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

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6. Electrical Characteristics

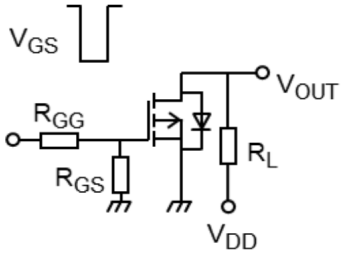
6.1. Static Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current	I_{GSS}	V_{GS} = -16/+10 V, V_{DS} = 0 V	—	—	±10	μA
Drain cut-off current	I_{DSS}	V_{DS} = -40 V, V_{GS} = 0 V	—	—	-10	
Drain-source breakdown voltage	$V_{(BR)DSS}$	I_D = -10 mA, V_{GS} = 0 V	-40	—	—	V
Drain-source breakdown voltage (Note 4)	$V_{(BR)DSX}$	I_D = -10 mA, V_{GS} = 10 V	-30	—	—	
Gate threshold voltage	V_{th}	V_{DS} = -10 V, I_D = -1 mA	-2.0	—	-3.0	
Drain-source on-resistance	$R_{DS(ON)}$	V_{GS} = -6 V, I_D = -40 A	—	5.1	7.9	mΩ
		V_{GS} = -10 V, I_D = -40 A	—	4.0	5.2	

Note 4: If a forward bias is applied between gate and source, this device enters $V_{(BR)DSX}$ mode. Note that the drain-source breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Input capacitance	C_{iss}	V_{DS} = -10 V, V_{GS} = 0 V, f = 1 MHz	—	7770	—	pF
Reverse transfer capacitance	C_{rss}		—	740	—	
Output capacitance	C_{oss}		—	970	—	
Switching time (rise time)	t_r	See Figure 6.2.1.	—	100	—	ns
Switching time (turn-on time)	t_{on}		—	125	—	
Switching time (fall time)	t_f		—	300	—	
Switching time (turn-off time)	t_{off}		—	970	—	



V_{DD} ≈ -20 V
V_{GS} = 0 V/-10 V
I_D = -40 A
R_L = 0.5 Ω
R_{GG} = R_{GS} = 4.7 Ω
Duty ≤ 1 %, t_w = 10 μs

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Q_g	V_{DD} ≈ -32 V, V_{GS} = -10 V, I_D = -80 A	—	158	—	nC
Gate-source charge	Q_{gs}		—	106	—	
Gate-drain charge	Q_{gd}		—	52	—	

6.4. Source-Drain Characteristics (T_a = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Reverse drain current (DC) (Note 5)	I_{DR}	—	—	—	-80	A
Reverse drain current (pulsed) (Note 5)	I_{DRP}	—	—	—	-160	
Diode forward voltage	V_{DSF}	I_{DR} = -80 A, V_{GS} = 0 V	—	—	1.2	V
Reverse recovery time	t_{rr}	I_{DR} = -80 A, V_{GS} = 0 V dI_{DR}/dt = 50 A/μs	—	50	—	ns
Reverse recovery charge	Q_{rr}		—	33	—	nC

Note 5: Ensure that the channel temperature does not exceed 175°C.

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7. Marking (Note)

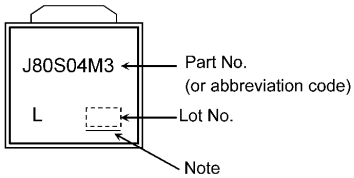


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.
Not underlined: [[Pb]]/INCLUDES > MCV
Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]
Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.
The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

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8. Characteristics Curves (Note)

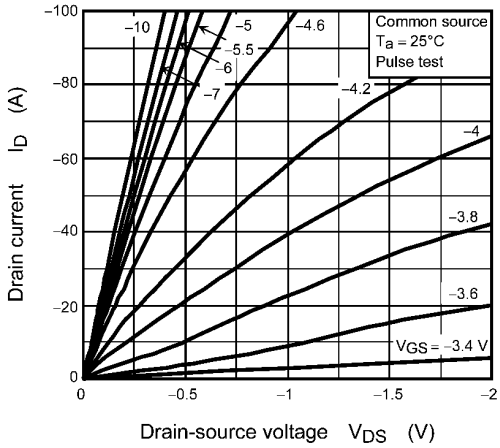


Fig. 8.1 I_D - V_{DS}

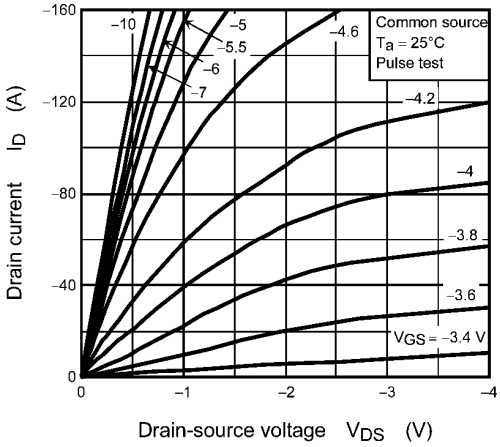


Fig. 8.2 I_D - V_{DS}

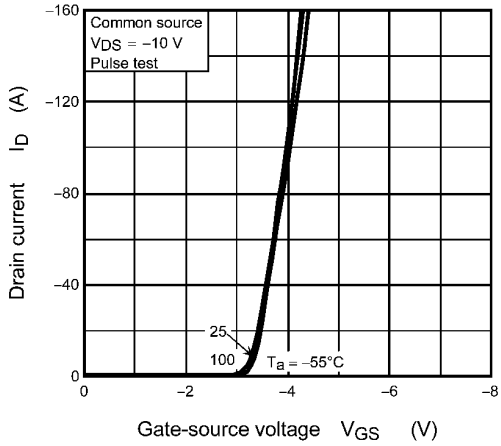


Fig. 8.3 I_D - V_{GS}

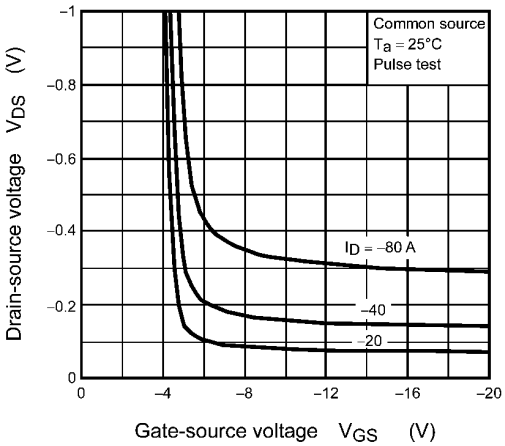


Fig. 8.4 V_{DS} - V_{GS}

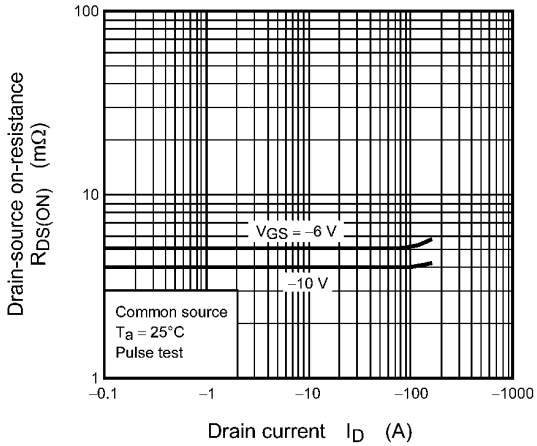


Fig. 8.5 $R_{DS(ON)}$ - I_D

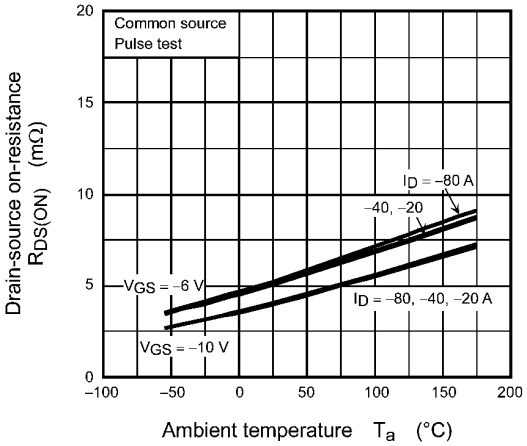


Fig. 8.6 $R_{DS(ON)}$ - T_a

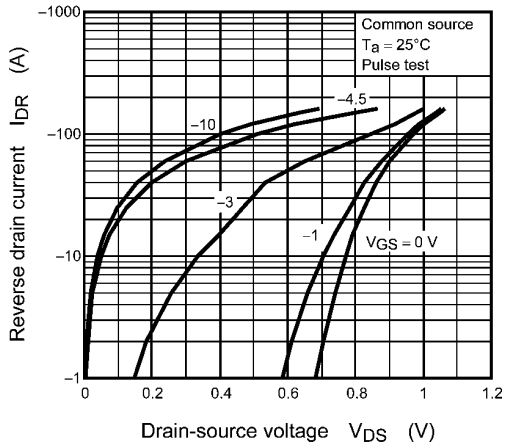


Fig. 8.7 I_{DR} - V_{DS}

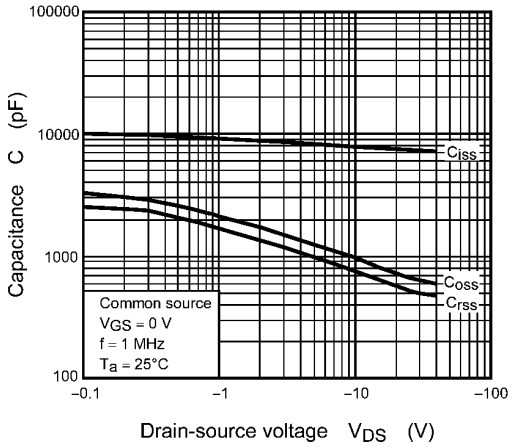


Fig. 8.8 Capacitance - V_{DS}

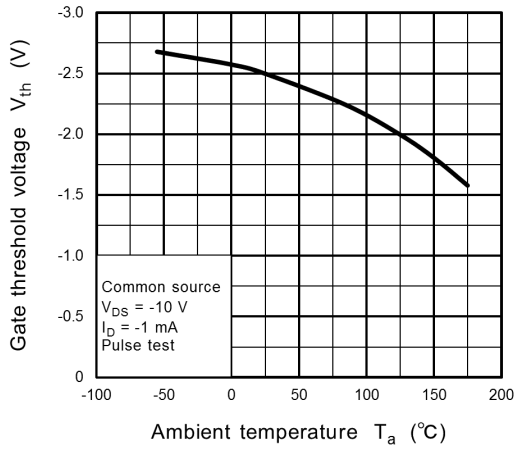


Fig. 8.9 V_{th} - T_a

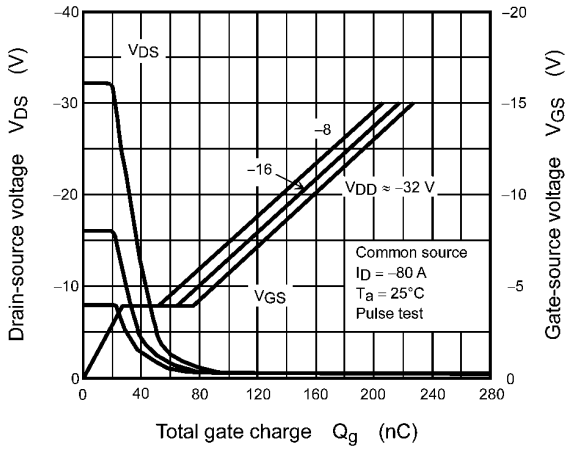


Fig. 8.10 Dynamic Input/Output Characteristics

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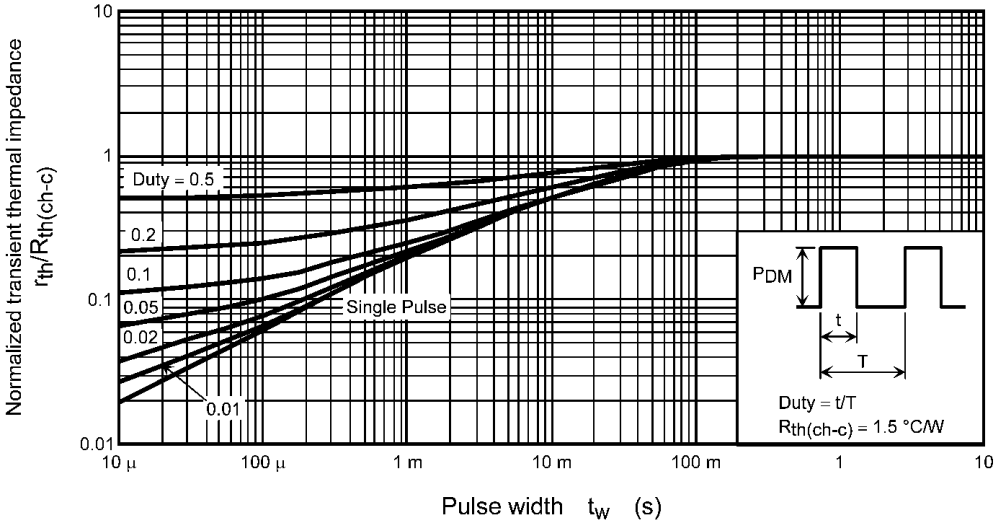


Fig. 8.11 $r_{th}/R_{th(ch-c)}$ - t_W (Guaranteed Maximum)

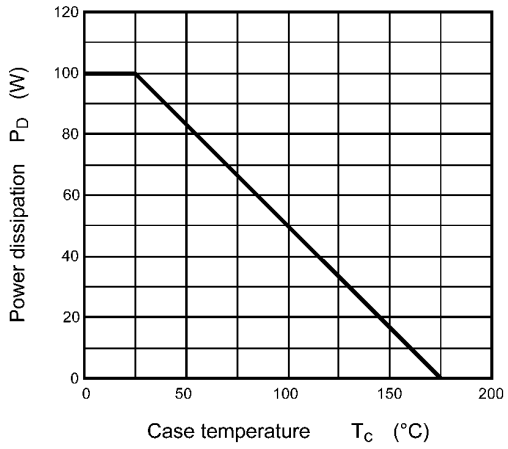


Fig. 8.12 P_D - T_C (Guaranteed Maximum)

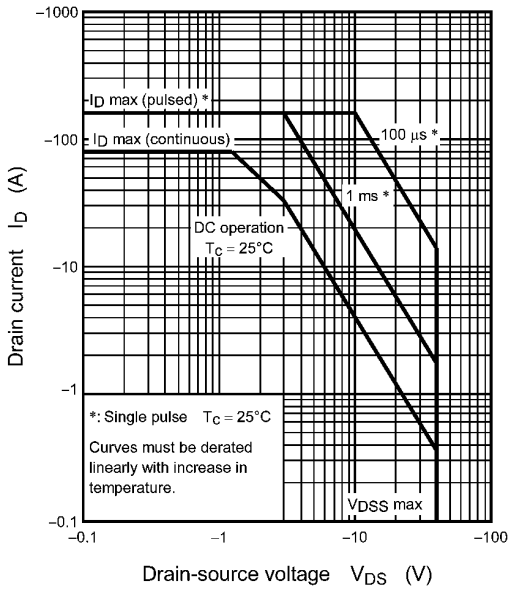


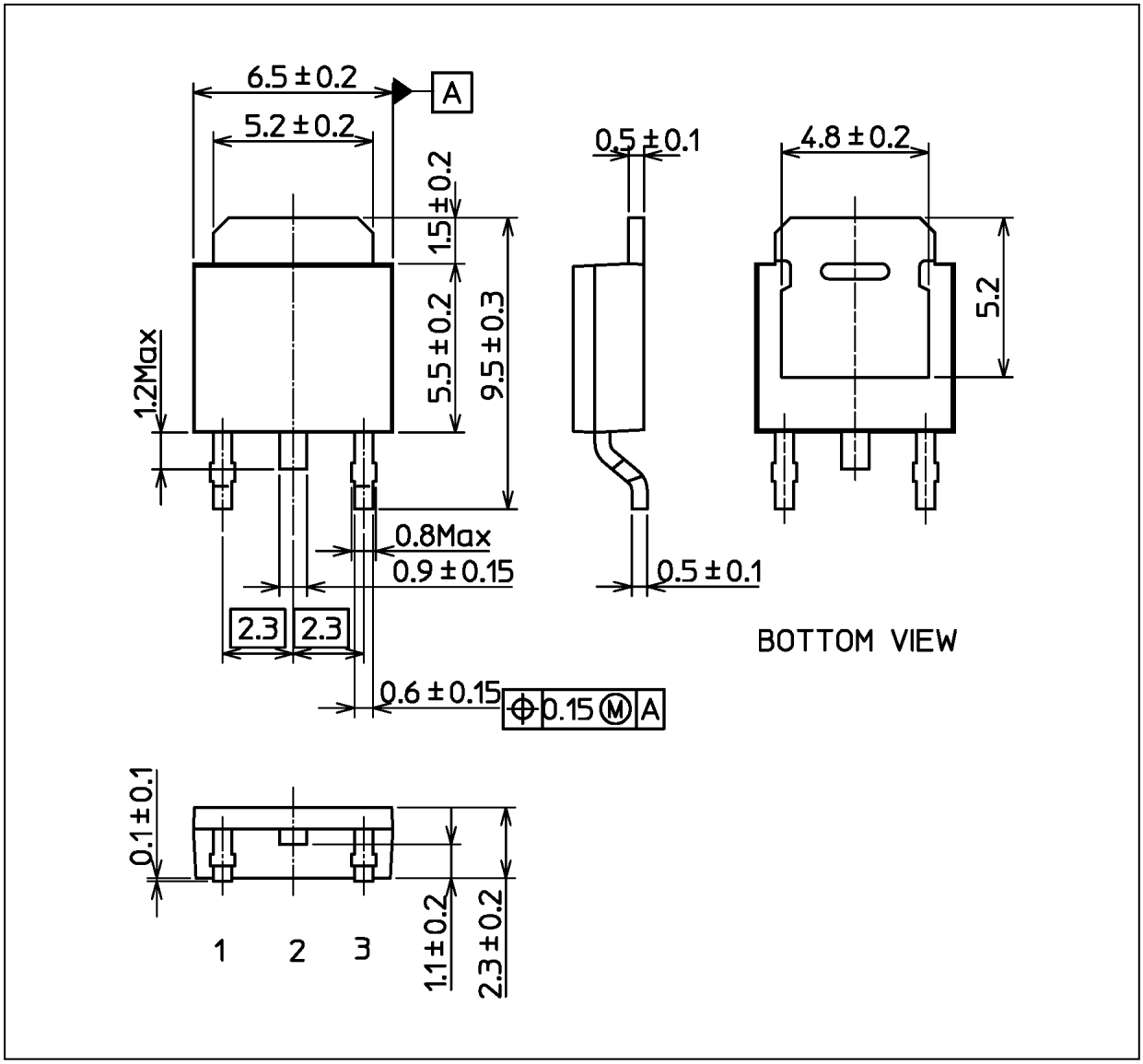
Fig. 8.13 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

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Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

Package Name(s)
TOSHIBA: 2-7M1A
Nickname: DPAK+

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